IN THE CLAIMS

Please amend claims 1-24 to the following:

1. (Previously Amended) A method comprising:

depositing a zeolite - solvent solution on an underlying layer;

removing at least some of the solvent from the zeolite – solvent solution to form a zeolite film; and

depositing a carbon doped oxide (CDO) in the zeolite film to form a zeolite – CDO composite film;

etching a via opening and a trench opening in CDO-zeolite composite film; forming a conductive material in the via opening and the trench opening.

- 2. (Original) The method of claim 1, wherein the solvent is water.
- 3. (Original) The method of claim 1, wherein the solvent is an organic oligomer.
- 4. (Original) The method of claim 3, wherein the organic oligomer is selected from a group consisting of polyethylene glycol, poly styrene, poly (Methacrylates), Poly (acrylate), or poly ethylene oxide.
- 5. (Original) The method of claim 1, wherein removing at least some of the solvent from the zeolite solvent solution comprises:

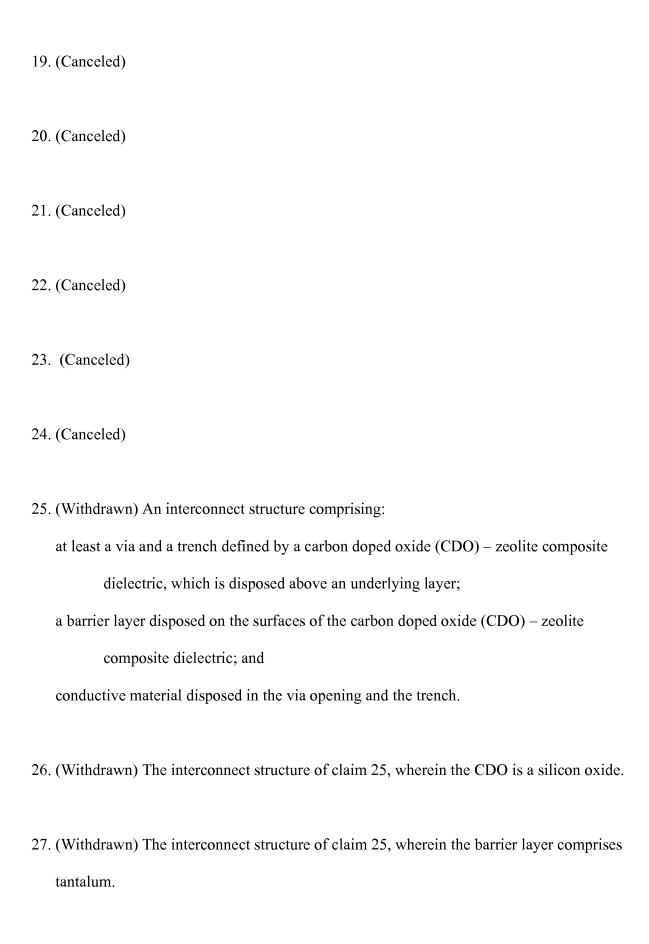
drying the zeolite – solvent solution.

6.	(Original) The method of claim 1, wherein removing at least some of the solvent from the
	zeolite – solvent solution comprises:
	vacuuming the zeolite – solvent solution.
7.	(Original) The method of claim 1, wherein depositing the zeolite - solvent solution on the
	underlying layer comprises:
	spin-coating the zeolite - solvent solution on the underlying layer.
8.	(Original) The method of claim 1, wherein depositing the zeolite - solvent solution on the
	underlying layer comprises:
	dip-coating the zeolite - solvent solution on the underlying layer.
9.	(Original) The method of claim 1, wherein depositing the CDO in the zeolite film
	comprises:
	chemical vapor deposition of the CDO in the zeolite film.
10.	(Original) The method of claim 1, wherein the CDO is a silicon oxide.
11.	(Original) The method claim 1, wherein the underlying layer is a wafer.
12.	(Original) The method claim 1, wherein the underlying layer is an interlayer dielectric layer.
13.	(Original) The method claim 12, wherein the interlayer dielectric layer comprises a zeolite –
	carbon doped oxide composite film.

- 14. (Original) The method of claim 1, further comprising calcinating the zeolite CDO composite film to form a solid phase zeolite CDO composite film.
- 15. (Original) The method claim 14, wherein calcinating the zeolite CDO composite film comprises:

heating the zeolite – CDO composite film; and cooling zeolite – CDO composite film.

- 16. (Original) The method of claim 15, wherein heating the zeolite CDO composite film is done in an oven.
- 17. (Original) The method of claim 16, wherein the oven is at a temperature in the range of 300°C to 550°C.
- 18. (Original) The method of claim 14, wherein the steps of depositing the zeolite solvent solution, removing at least some of the solvent from the zeolite solvent solution, and depositing a CDO are repeated before calcinating the zeolite CDO composite film to achieve a thicker zeolite CDO composite film.



28	. (Withdrawn) The interconnect structure of claim 2	25, whereir	the conductive	material
	comprises a copper alloy.			

29. (Withdrawn) The interconnect structure of claim 25, wherein the underlying layer is a wafer.